

AMC1350 高精度、 $\pm 5V$ 入力、強化絶縁型アンプ

1 特長

- リニア入力電圧範囲: $\pm 5V$
- 高い入力インピーダンス: $1.25M\Omega$ (標準値)
- 固定ゲイン: $0.4V/V$
- 小さい DC 誤差:
 - オフセット誤差: $\pm 1.5mV$ (最大値)
 - オフセット・ドリフト: $\pm 15\mu V/^\circ C$ (最大値)
 - ゲイン誤差: $\pm 0.2\%$ (最大値)
 - ゲイン・ドリフト: $\pm 35ppm/^\circ C$ (最大値)
 - 非直線性: $\pm 0.02\%$ (最大値)
- ハイサイド、ローサイドでの動作: $3.3V$ または $5V$
- 高い CMTI: $100kV/\mu s$ (最小値)
- フェイルセーフ出力
- 安全関連の認証:
 - DIN VDE V 0884-11 に準拠した強化絶縁耐圧: $7070V_{PK2017-01}$
 - UL 1577 に準拠した絶縁耐圧: $5000V_{RMS}$ (1 分間)
- 拡張産業用温度範囲全体にわたって仕様を完全に規定: $-40^\circ C \sim +125^\circ C$

2 アプリケーション

- 次の用途での絶縁型 AC 電圧センシング:
 - モーター・ドライブ
 - 周波数インバータ
 - 保護リレー
 - 電源

3 概要

AMC1350 は高精度の絶縁型アンプで、磁気干渉に対して高い耐性のある絶縁バリアにより、入力側と出力側の回路が分離されています。この絶縁バリアは、VDE V 0884-11 および UL1577 に従って最大 $5kV_{RMS}$ の強化ガルバニック絶縁を達成していることが認証されており、最大 $1.5kV_{RMS}$ の使用電圧に対応しています。

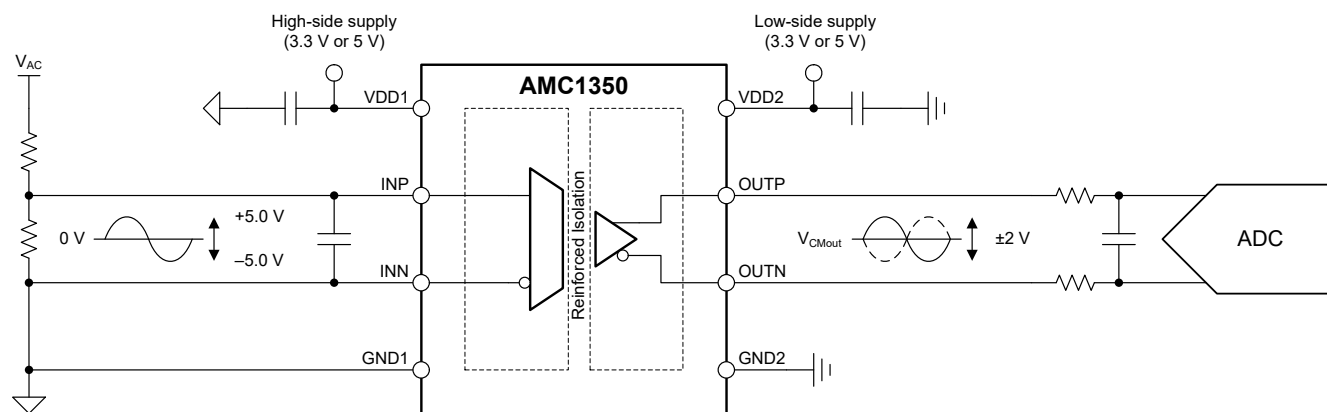
この絶縁バリアは、異なる同相電圧レベルで動作するシステム領域を分離し、潜在的に危険な電圧と損傷から低電圧側を保護します。

AMC1350 の高インピーダンス入力は、高インピーダンスの抵抗分圧器や出力抵抗の高い他の電圧信号源と接続するよう最適化されています。優れた精度と低い温度ドリフトにより、拡張産業用温度範囲の $-40^\circ C \sim +125^\circ C$ にわたって、DC/DC コンバータ、周波数インバータ、AC モーター、サーボ・ドライブ・アプリケーションで高精度の AC および DC 電圧センシングをサポートします。

製品情報⁽¹⁾

部品番号	パッケージ	本体サイズ (公称)
AMC1350	SOIC (8)	5.85mm × 7.50mm

- (1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



代表的なアプリケーション



Table of Contents

1 特長	1	7.1 Overview.....	19
2 アプリケーション	1	7.2 Functional Block Diagram.....	19
3 概要	1	7.3 Feature Description.....	19
4 Revision History	2	7.4 Device Functional Modes.....	21
5 Pin Configuration and Functions	3	8 Application and Implementation	22
6 Specifications	4	8.1 Application Information.....	22
6.1 Absolute Maximum Ratings.....	4	8.2 Typical Application.....	22
6.2 ESD Ratings.....	4	8.3 What To Do and What Not To Do.....	27
6.3 Recommended Operating Conditions.....	4	9 Power Supply Recommendations	27
6.4 Thermal Information.....	5	10 Layout	28
6.5 Power Ratings.....	5	10.1 Layout Guidelines.....	28
6.6 Insulation Specifications.....	6	10.2 Layout Example.....	28
6.7 Safety-Related Certifications.....	7	11 Device and Documentation Support	29
6.8 Safety Limiting Values.....	7	11.1 Documentation Support.....	29
6.9 Electrical Characteristics.....	8	11.2 Receiving Notification of Documentation Updates..	29
6.10 Switching Characteristics.....	10	11.3 サポート・リソース.....	29
6.11 Timing Diagram.....	10	11.4 Trademarks.....	29
6.12 Insulation Characteristics Curves.....	11	11.5 Electrostatic Discharge Caution.....	29
6.13 Typical Characteristics.....	12	11.6 Glossary.....	29
7 Detailed Description	19		

4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (August 2021) to Revision A (December 2021)	Page
• ドキュメントのステータスを「事前情報」から「量産データ」に変更.....	1

5 Pin Configuration and Functions

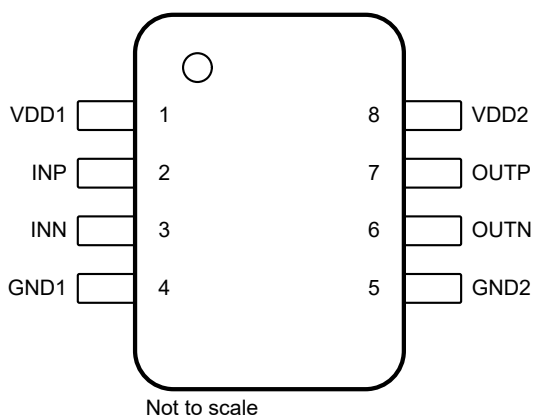


图 5-1. DWV Package, 8-Pin SOIC, Top View

表 5-1. Pin Functions

PIN		TYPE	DESCRIPTION
NO.	NAME		
1	VDD1	High-side power	High-side power supply ⁽¹⁾
2	INP	Analog input	Noninverting analog input. Either INP or INN must have a DC current path to GND1 to define the common-mode input voltage. ⁽²⁾
3	INN	Analog input	Inverting analog input. Either INP or INN must have a DC current path to GND1 to define the common-mode input voltage. ⁽²⁾
4	GND1	High-side ground	High-side analog ground
5	GND2	Low-side ground	Low-side analog ground
6	OUTN	Analog output	Inverting analog output
7	OUTP	Analog output	Noninverting analog output
8	VDD2	Low-side power	Low-side power supply ⁽¹⁾

(1) See the [Power Supply Recommendations](#) section for power-supply decoupling recommendations.

(2) See the [Layout](#) section for details.

6 Specifications

6.1 Absolute Maximum Ratings

see⁽¹⁾

		MIN	MAX	UNIT
Power-supply voltage	High-side VDD1 to GND1	−0.3	6.5	V
	Low-side VDD2 to GND2	−0.3	6.5	
Analog input voltage	INP, INN	−15	15	V
Analog output voltage	OUTP, OUTN	GND2 − 0.5	VDD2 + 0.5	V
Input current	Continuous, any pin except power-supply pins	−10	10	mA
Temperature	Junction, T _J		150	°C
	Storage, T _{stg}	−65	150	

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
POWER SUPPLY						
VDD1	High-side power-supply	VDD1 to GND1	3	5	5.5	V
VDD2	Low-side power-supply	VDD2 to GND2	3	3.3	5.5	V
ANALOG INPUT						
V _{Clipping}	Input voltage before clipping output	V _{IN} = V _{INP} − V _{INN}		±6.25		V
V _{FSR}	Specified linear full-scale voltage	V _{IN} = V _{INP} − V _{INN}	−5		5	V
V _{CM}	Operating common-mode input voltage		−4		4	V
ANALOG OUTPUT						
C _{LOAD}	Capacitive load	On OUTP or OUTN to GND2			500	pF
		OUTP to OUTN			250	
R _{LOAD}	Resistive load	On OUTP or OUTN to GND2		10	1	kΩ
TEMPERATURE RANGE						
T _A	Operating ambient temperature		−55		125	°C
	Specified ambient temperature		−40		125	

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		AMC1350	UNIT
		DWV (SOIC)	
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	84.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	28.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	41.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	4.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	39.1	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Power Ratings

PARAMETER		TEST CONDITIONS	VALUE	UNIT
P_D	Maximum power dissipation (both sides)	VDD1 = VDD2 = 5.5 V	96	mW
P_{D1}	Maximum power dissipation (high-side)	VDD1 = 3.6 V	29	mW
		VDD1 = 5.5 V	51	
P_{D2}	Maximum power dissipation (low-side)	VDD2 = 3.6 V	26	mW
		VDD2 = 5.5 V	45	

6.6 Insulation Specifications

over operating ambient temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	VALUE	UNIT
GENERAL				
CLR	External clearance ⁽¹⁾	Shortest pin-to-pin distance through air	≥ 8.5	mm
CPG	External creepage ⁽¹⁾	Shortest pin-to-pin distance across the package surface	≥ 8.5	mm
DTI	Distance through insulation	Minimum internal gap (internal clearance) of the double insulation	≥ 0.021	mm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	≥ 600	V
	Material group	According to IEC 60664-1	I	
	Overvoltage category per IEC 60664-1	Rated mains voltage ≤ 600 V _{RMS}	I-IV	
		Rated mains voltage ≤ 1000 V _{RMS}	I-III	
DIN VDE V 0884-11 (VDE V 0884-11): 2017-01				
V _{IORM}	Maximum repetitive peak isolation voltage	At AC voltage	2120	V _{PK}
V _{IOWM}	Maximum-rated isolation working voltage	At AC voltage (sine wave)	1500	V _{RMS}
		At DC voltage	2120	V _{DC}
V _{IOTM}	Maximum transient isolation voltage	V _{TEST} = V _{IOTM} , t = 60 s (qualification test)	7070	V _{PK}
		V _{TEST} = 1.2 × V _{IOTM} , t = 1 s (100% production test)	8480	
V _{IOSM}	Maximum surge isolation voltage ⁽²⁾	Test method per IEC 60065, 1.2/50-μs waveform, V _{TEST} = 1.6 × V _{IOSM} = 12800 V _{PK} (qualification)	8000	V _{PK}
q _{pd}	Apparent charge ⁽³⁾	Method a, after input/output safety test subgroups 2 and 3, V _{ini} = V _{IOTM} , t _{ini} = 60 s, V _{pd(m)} = 1.2 × V _{IORM} , t _m = 10 s	≤ 5	pC
		Method a, after environmental tests subgroup 1, V _{ini} = V _{IOTM} , t _{ini} = 60 s, V _{pd(m)} = 1.6 × V _{IORM} , t _m = 10 s	≤ 5	
		Method b1, at routine test (100% production) and preconditioning (type test), V _{ini} = V _{IOTM} , t _{ini} = 1 s, V _{pd(m)} = 1.875 × V _{IORM} , t _m = 1 s	≤ 5	
C _{IO}	Barrier capacitance, input to output ⁽⁴⁾	V _{IO} = 0.5 V _{PP} at 1 MHz	~1.5	pF
R _{IO}	Insulation resistance, input to output ⁽⁴⁾	V _{IO} = 500 V at T _A = 25°C	> 10 ¹²	Ω
		V _{IO} = 500 V at 100°C ≤ T _A ≤ 125°C	> 10 ¹¹	
		V _{IO} = 500 V at T _S = 150°C	> 10 ⁹	
	Pollution degree		2	
	Climatic category		55/125/21	
UL1577				
V _{ISO}	Withstand isolation voltage	V _{TEST} = V _{ISO} = 5000 V _{RMS} or 7071 V _{DC} , t = 60 s (qualification), V _{TEST} = 1.2 × V _{ISO} = 6000 V _{RMS} , t = 1 s (100% production test)	5000	V _{RMS}

- (1) Apply creepage and clearance requirements according to the specific equipment isolation standards of an application. Care must be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed circuit board (PCB) do not reduce this distance. Creepage and clearance on a PCB become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a PCB are used to help increase these specifications.
- (2) Testing is carried out in air or oil to determine the intrinsic surge immunity of the isolation barrier.
- (3) Apparent charge is electrical discharge caused by a partial discharge (pd).
- (4) All pins on each side of the barrier are tied together, creating a two-pin device.

6.7 Safety-Related Certifications

VDE	UL
Certified according to DIN VDE V 0884-11 (VDE V 0884-11): 2017-01, DIN EN 60950-1 (VDE 0805 Teil 1): 2014-08, and DIN EN 60065 (VDE 0860): 2005-11	Recognized under 1577 component recognition
Reinforced insulation	Single protection
Certificate number: pending	File number: E181974

6.8 Safety Limiting Values

Safety limiting⁽¹⁾ intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to over-heat the die and damage the isolation barrier potentially leading to secondary system failures.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I _S	Safety input, output, or supply current	R _{θJA} = 84.6°C/W, VDDx = 5.5 V, T _J = 150°C, T _A = 25°C			270	mA
		R _{θJA} = 84.6°C/W, VDDx = 3.6 V, T _J = 150°C, T _A = 25°C			410	
P _S	Safety input, output, or total power	R _{θJA} = 84.6°C/W, T _J = 150°C, T _A = 25°C			1480	mW
T _S	Maximum safety temperature				150	°C

- (1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power, respectively. Do not exceed the maximum limits of I_S and P_S. These limits vary with the ambient temperature, T_A.

The junction-to-air thermal resistance, R_{θJA}, in the [Thermal Information](#) table is that of a device installed on a high-K test board for leaded surface-mount packages. Use these equations to calculate the value for each parameter:

T_J = T_A + R_{θJA} × P, where P is the power dissipated in the device.

T_{J(max)} = T_S = T_A + R_{θJA} × P_S, where T_{J(max)} is the maximum junction temperature.

P_S = I_S × VDD_{max}, where VDD_{max} is the maximum supply voltage for high-side and low-side.

6.9 Electrical Characteristics

minimum and maximum specifications apply from $T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $V_{DD1} = 3.0\text{ V}$ to 5.5 V , $V_{DD2} = 3.0\text{ V}$ to 5.5 V , $\text{INP} = -5\text{ V}$ to $+5\text{ V}$, and $\text{INN} = \text{GND1}$ (unless otherwise noted); typical specifications are at $T_A = 25^{\circ}\text{C}$, $V_{DD1} = 5\text{ V}$, and $V_{DD2} = 3.3\text{ V}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
ANALOG INPUT						
V_{OS}	Offset voltage ⁽²⁾	$T_A = 25^{\circ}\text{C}$, $\text{INN} = \text{INP} = \text{GND1}$, $4.5\text{ V} \leq V_{DD1} \leq 5.5\text{ V}$ ⁽¹⁾	-1.5	± 0.3	1.5	mV
		$T_A = 25^{\circ}\text{C}$, $\text{INN} = \text{INP} = \text{GND1}$, $3.0\text{ V} \leq V_{DD1} \leq 5.5\text{ V}$ ⁽³⁾	-2.5	-0.8	2.5	
ΔV_{OS}	Offset voltage long-term stability	10 years at $T_A = 55^{\circ}\text{C}$		0 ⁽⁷⁾		mV
TCV_{OS}	Offset voltage thermal drift ⁽⁵⁾	$\text{INN} = \text{INP} = \text{GND1}$	-15	± 3	15	$\mu\text{V}/^{\circ}\text{C}$
ΔTCV_{OS}	Offset voltage thermal drift long-term stability	10 years at $T_A = 55^{\circ}\text{C}$, $\text{INN} = \text{INP} = \text{GND1}$		0 ⁽⁷⁾		$\text{mV}/^{\circ}\text{C}$
R_{IN}	Input resistance, differential		2	2.5	3	M Ω
	Input resistance, single ended	$\text{INN} = \text{GND1}$	1	1.25	1.5	
ΔR_{IN}	Input resistance long-term stability	10 years at $T_A = 55^{\circ}\text{C}$		0 ⁽⁷⁾		ppm
TCR_{IN}	Input resistance thermal drift	$-40^{\circ}\text{C} \leq T_A \leq 85^{\circ}\text{C}$		5		$\text{ppm}/^{\circ}\text{C}$
C_{IN}	Single-ended input capacitance	$\text{INN} = \text{HGND}$, $f_{IN} = 275\text{ kHz}$		4		pF
C_{IND}	Differential input capacitance	$f_{IN} = 275\text{ kHz}$		2		pF
ANALOG OUTPUT						
	Nominal gain			0.40		V/V
E_G	Gain error ⁽¹⁾	$T_A = 25^{\circ}\text{C}$	-0.2%	$\pm 0.05\%$	0.2%	
ΔE_G	Gain error long-term stability	10 years at $T_A = 55^{\circ}\text{C}$		0 ⁽⁷⁾		
TCE_G	Gain error thermal drift ^{(1) (6)}		-35	± 10	35	$\text{ppm}/^{\circ}\text{C}$
ΔTCE_G	Gain error thermal drift long-term stability	10 years at $T_A = 55^{\circ}\text{C}$		0 ⁽⁷⁾		$\text{ppm}/^{\circ}\text{C}$
	Nonlinearity ⁽¹⁾		-0.02%	$\pm 0.003\%$	0.02%	
	Nonlinearity thermal drift			0.2		$\text{ppm}/^{\circ}\text{C}$
THD	Total harmonic distortion ⁽⁴⁾	$V_{IN} = 10\text{ V}_{PP}$, $f_{IN} = 10\text{ kHz}$, $\text{BW} = 100\text{ kHz}$		-87		dB
SNR	Signal-to-noise ratio	$V_{IN} = 10\text{ V}_{PP}$, $f_{IN} = 1\text{ kHz}$, $\text{BW} = 10\text{ kHz}$	81	85		dB
		$V_{IN} = 10\text{ V}_{PP}$, $f_{IN} = 10\text{ kHz}$, $\text{BW} = 100\text{ kHz}$		75		
	Output noise	$\text{INN} = \text{INP} = \text{GND1}$, $\text{BW} = 100\text{ kHz}$		250		μV_{rms}
CMRR	Common-mode rejection ratio	DC, $\text{INN} = \text{INP}$, $V_{CM\text{ min}} \leq V_{CM} \leq V_{CM\text{ max}}$		-72		dB
		$f_{IN} = 10\text{ kHz}$, $\text{INN} = \text{INP} = 10\text{ V}_{PP}$		-71		
PSRR	Power-supply rejection ratio ⁽²⁾	PSRR vs V_{DD1} , DC		-67		dB
		PSRR vs V_{DD2} , DC		-80		
		PSRR vs V_{DD1} with 10-kHz, 100-mV ripple		-65		
		PSRR vs V_{DD2} with 10-kHz, 100-mV ripple		-64		
V_{CMout}	Output common-mode voltage		1.39	1.44	1.49	V
$V_{CLIPout}$	Clipping differential output voltage	$V_{OUT} = (V_{OUTP} - V_{OUTN})$, $V_{IN} > V_{Clipping}$		2.49		V
$V_{Fail-safe}$	Fail-safe differential output voltage	V_{DD1} undervoltage or V_{DD1} missing		-2.57	-2.5	V
BW	Output bandwidth		275	300		kHz
R_{OUT}	Output resistance	On OUTP or OUTN		< 0.2		Ω

6.9 Electrical Characteristics (continued)

minimum and maximum specifications apply from $T_A = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $V_{DD1} = 3.0\text{ V}$ to 5.5 V , $V_{DD2} = 3.0\text{ V}$ to 5.5 V , $\text{INP} = -5\text{ V}$ to $+5\text{ V}$, and $\text{INN} = \text{GND1}$ (unless otherwise noted); typical specifications are at $T_A = 25^{\circ}\text{C}$, $V_{DD1} = 5\text{ V}$, and $V_{DD2} = 3.3\text{ V}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Output short-circuit current	On OUTP or OUTN, sourcing or sinking, $\text{INN} = \text{INP} = \text{GND1}$, outputs shorted to either GND or VDD2		14		mA
CMTI	Common-mode transient immunity		100	150		kV/ μs
POWER SUPPLY						
VDD1 _{UV}	VDD1 undervoltage detection threshold	VDD1 rising	2.5	2.7	2.9	V
		VDD1 falling	2.4	2.6	2.8	
VDD2 _{UV}	VDD2 undervoltage detection threshold	VDD2 rising	2.2	2.45	2.65	V
		VDD2 falling	1.85	2.0	2.2	
I _{DD1}	High-side supply current	$3.0\text{ V} < V_{DD1} < 3.6\text{ V}$		6.0	8.1	mA
		$4.5\text{ V} < V_{DD1} < 5.5\text{ V}$		7.0	9.3	
I _{DD2}	Low-side supply current	$3.0\text{ V} < V_{DD2} < 3.6\text{ V}$		5.3	7.2	mA
		$4.5\text{ V} < V_{DD2} < 5.5\text{ V}$		5.9	8.1	

- (1) The typical value includes one standard deviation (*sigma*) at nominal operating conditions.
- (2) This parameter is input referred.
- (3) The typical value is at $V_{DD1} = 3.3\text{ V}$.
- (4) THD is the ratio of the rms sum of the amplitudes of first five higher harmonics to the amplitude of the fundamental.
- (5) Offset error temperature drift is calculated using the box method, as described by the following equation:

$$TCV_{OS} = (V_{OS,MAX} - V_{OS,MIN}) / \text{TempRange}$$
where $V_{OS,MAX}$ and $V_{OS,MIN}$ refer to the maximum and minimum V_{OS} values measured within the temperature range (-40 to 125°C).
- (6) Gain error temperature drift is calculated using the box method, as described by the following equation:

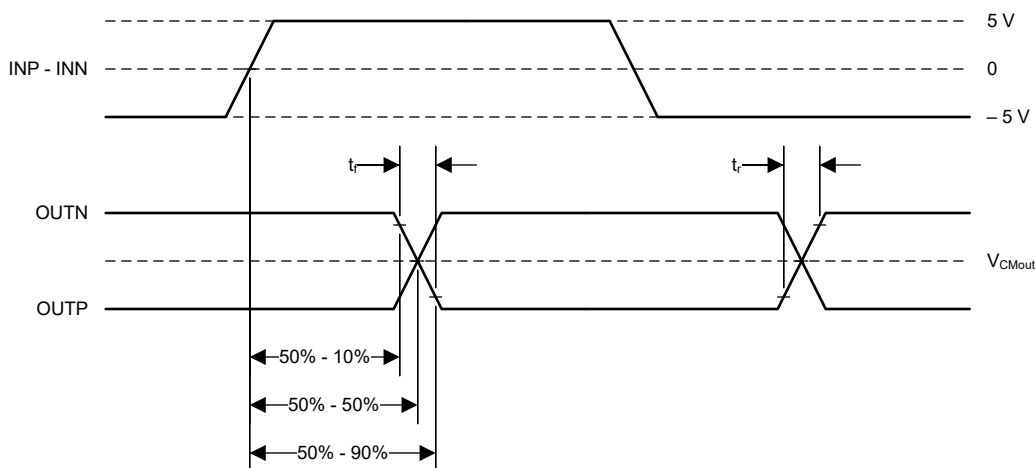
$$TCE_G (\text{ppm}) = ((E_{G,MAX} - E_{G,MIN}) / \text{TempRange}) \times 10^4$$
where $E_{G,MAX}$ and $E_{G,MIN}$ refer to the maximum and minimum E_G values (in %) measured within the temperature range (-40 to 125°C).
- (7) Value is below measurement capability.

6.10 Switching Characteristics

over operating ambient temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_r	Output signal rise time			1.3		μs
t_f	Output signal fall time			1.3		μs
	IN to OUTx signal delay (50% – 10%)	Unfiltered output		1	1.5	μs
	IN to OUTx signal delay (50% – 50%)	Unfiltered output		1.6	2.1	μs
	IN to OUTx signal delay (50% – 90%)	Unfiltered output		2.5	3	μs
t_{AS}	Analog settling time	VDD1 step to 3.0 V with VDD2 $\geq$ 3.0 V, to V_{OUTP} and V_{OUTN} valid, 0.1% settling		500	800	μs

6.11 Timing Diagram



6-1. Rise, Fall, and Delay Time Definition

6.12 Insulation Characteristics Curves

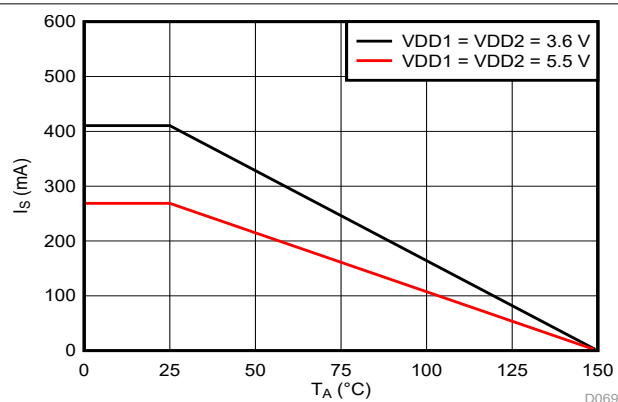


Figure 6-2. Thermal Derating Curve for Safety-Limiting Current per VDE

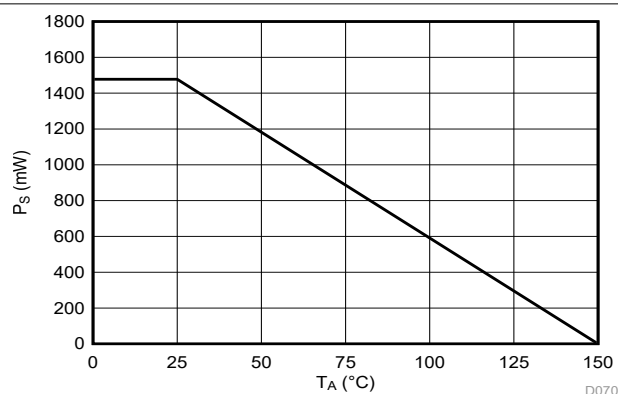
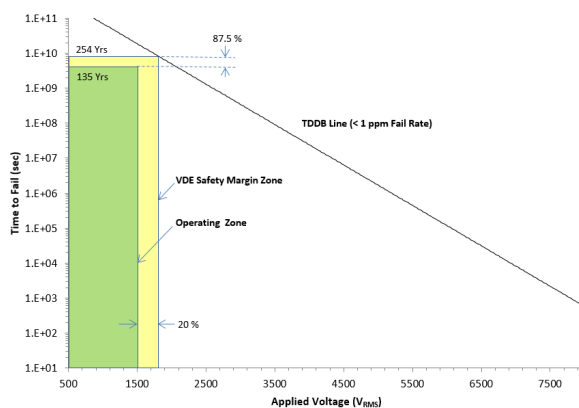


Figure 6-3. Thermal Derating Curve for Safety-Limiting Power per VDE



TA up to 150°C, stress-voltage frequency = 60 Hz, isolation working voltage = 1500 VRMS, operating lifetime = 135 years

Figure 6-4. Reinforced Isolation Capacitor Lifetime Projection

6.13 Typical Characteristics

at VDD1 = 5 V, VDD2 = 3.3 V, INN = GND1, INP = -5 V to 5 V, and $f_{IN} = 10$ kHz (unless otherwise noted)

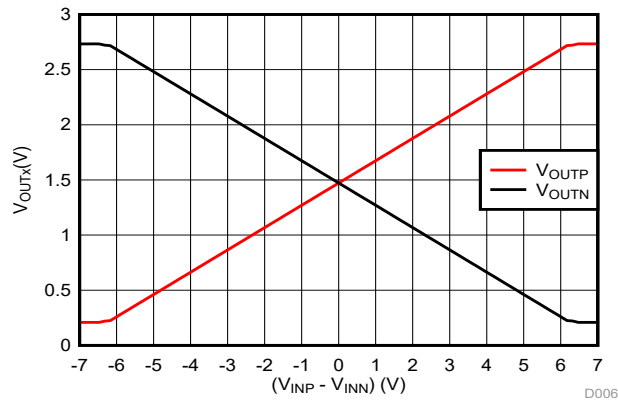
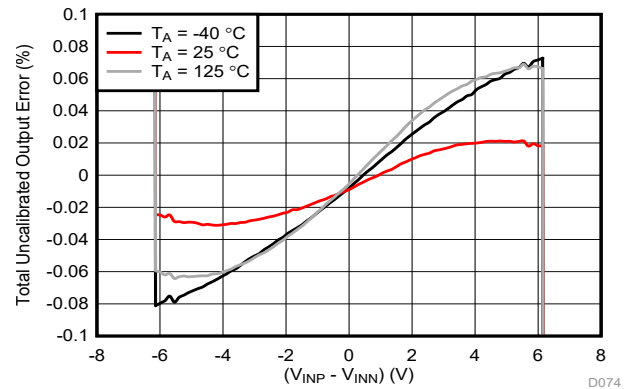


Figure 6-5. Output Voltage vs Input Voltage



Total uncalibrated output error is defined as:
 $(V_{OUT} - V_{IN} \times G) / (V_{Clipping} \times G)$ where $V_{IN} = (V_{INP} - V_{INN})$,
 G is the nominal gain of the device (0.4 V/V),
 and $V_{Clipping}$ is 6.25 V

Figure 6-6. Total Uncalibrated Output Error vs Input Voltage

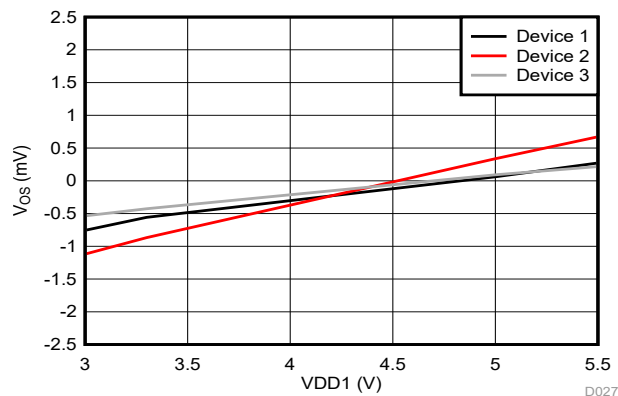


Figure 6-7. Input Offset Voltage vs High-Side Supply Voltage

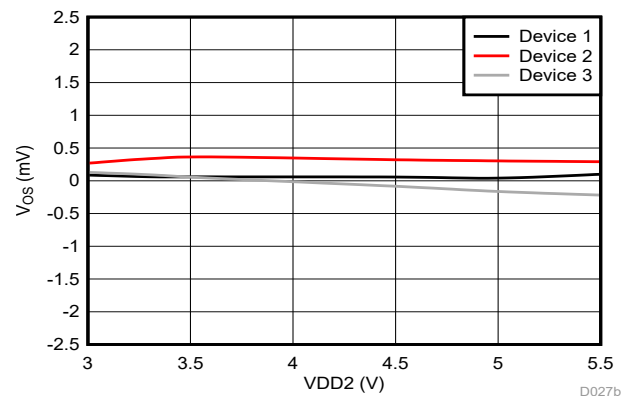


Figure 6-8. Input Offset Voltage vs Low-Side Supply Voltage

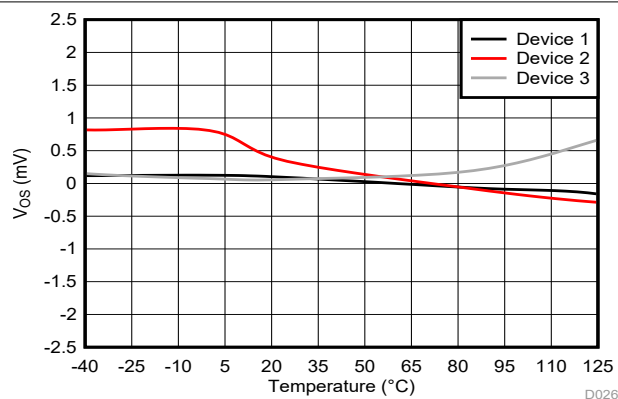


Figure 6-9. Input Offset Voltage vs Temperature

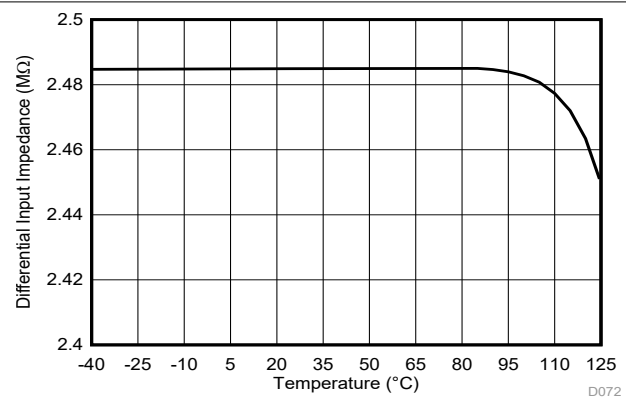


Figure 6-10. Differential Input Impedance vs Temperature

6.13 Typical Characteristics (continued)

at VDD1 = 5 V, VDD2 = 3.3 V, INN = GND1, INP = -5 V to 5 V, and $f_{IN} = 10$ kHz (unless otherwise noted)

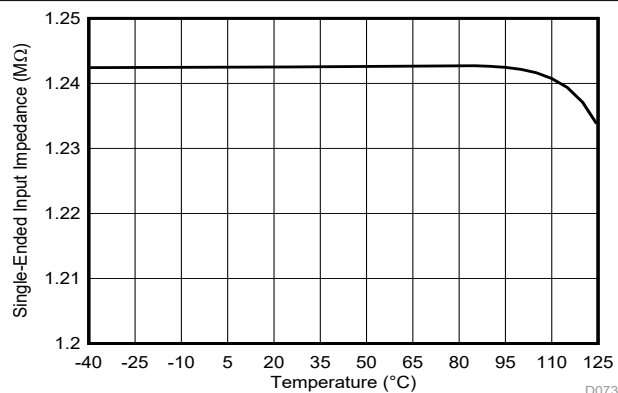


Figure 6-11. Single-Ended Input Impedance vs Temperature

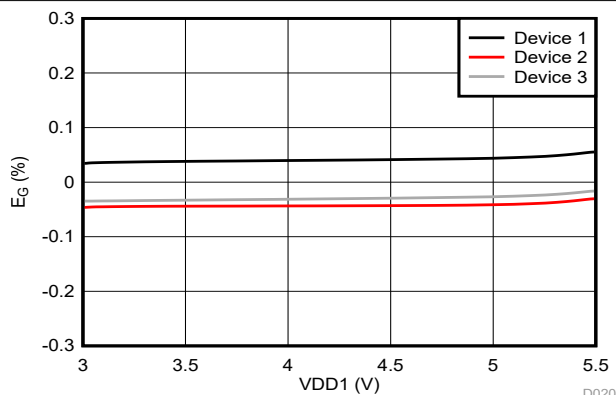


Figure 6-12. Gain Error vs High-Side Supply Voltage

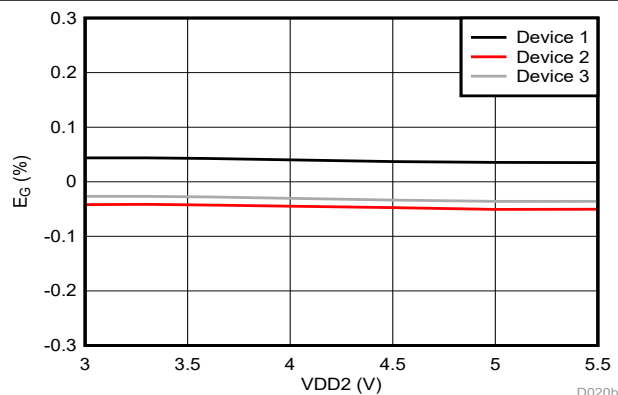


Figure 6-13. Gain Error vs Low-Side Supply Voltage

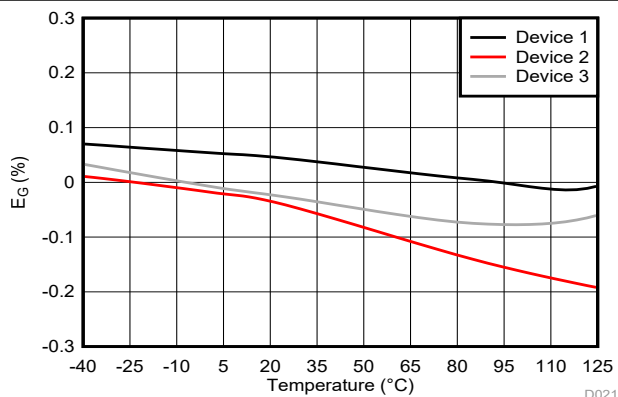


Figure 6-14. Gain Error vs Temperature

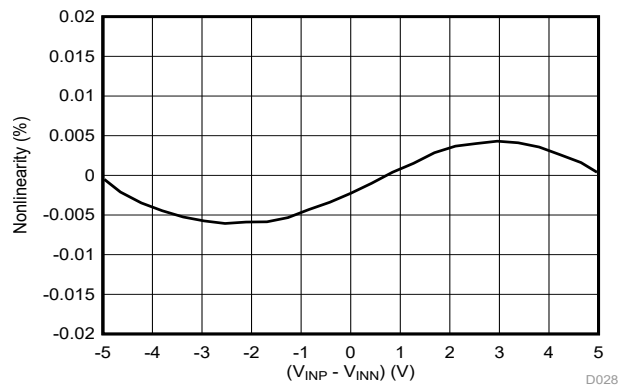


Figure 6-15. Nonlinearity vs Input Voltage

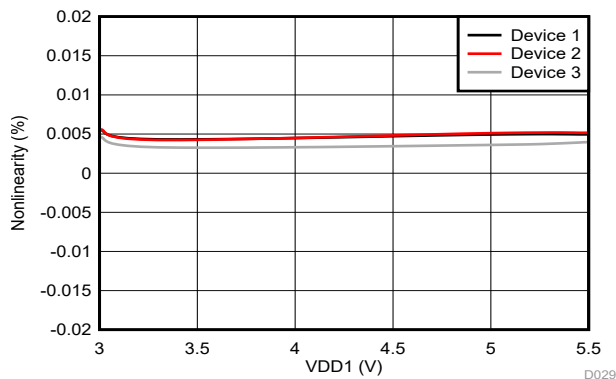
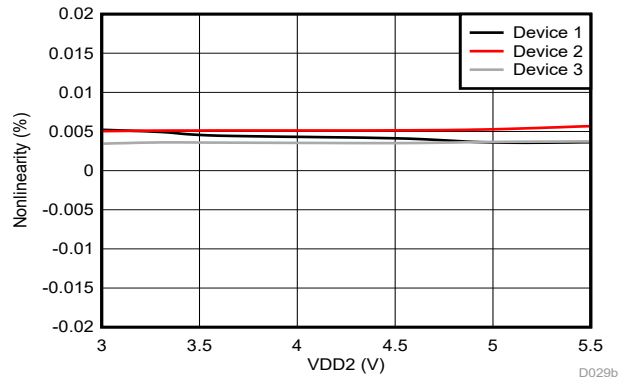


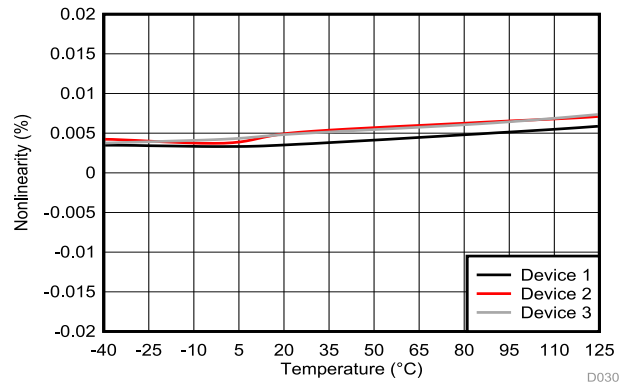
Figure 6-16. Nonlinearity vs High-Side Supply Voltage

6.13 Typical Characteristics (continued)

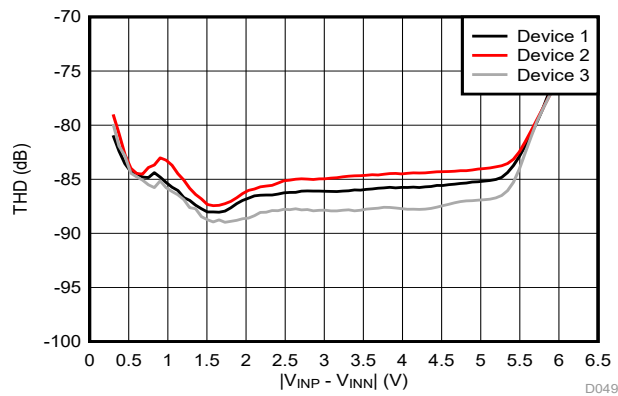
at VDD1 = 5 V, VDD2 = 3.3 V, INN = GND1, INP = -5 V to 5 V, and $f_{IN} = 10$ kHz (unless otherwise noted)



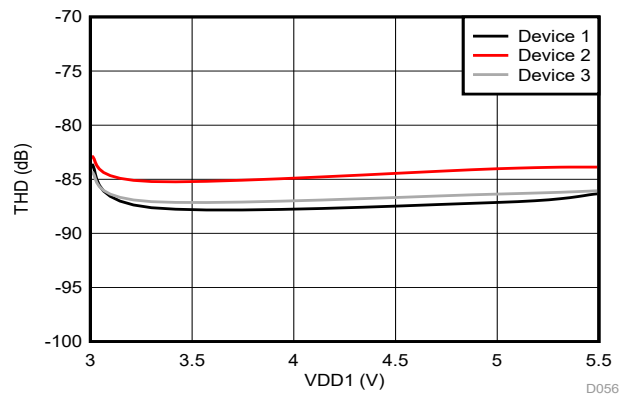
6-17. Nonlinearity vs Low-Side Supply Voltage



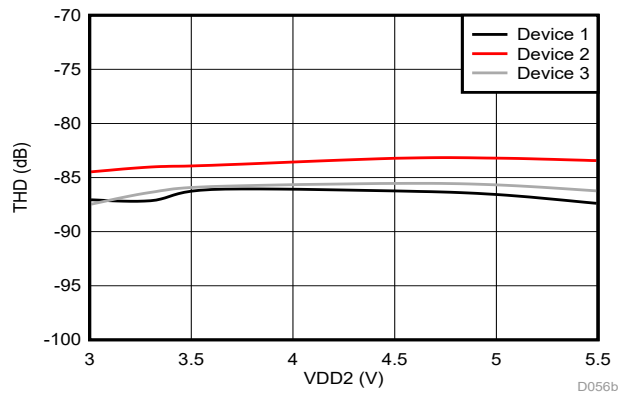
6-18. Nonlinearity vs Temperature



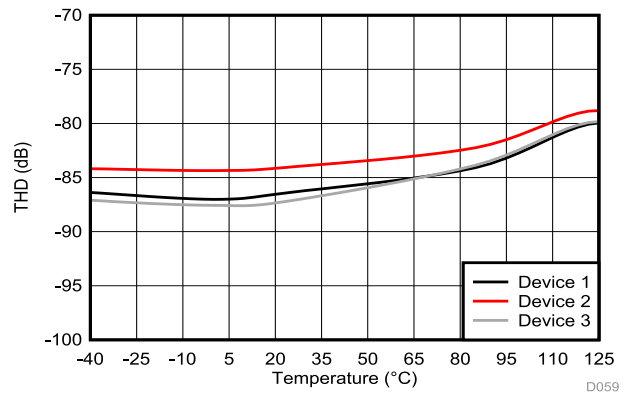
6-19. Total Harmonic Distortion vs Input Voltage



6-20. Total Harmonic Distortion vs High-Side Supply Voltage



6-21. Total Harmonic Distortion vs Low-Side Supply Voltage



6-22. Total Harmonic Distortion vs Temperature

6.13 Typical Characteristics (continued)

at VDD1 = 5 V, VDD2 = 3.3 V, INN = GND1, INP = -5 V to 5 V, and $f_{IN} = 10$ kHz (unless otherwise noted)

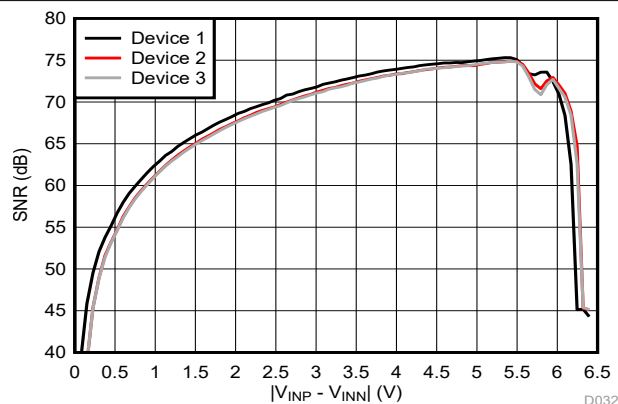


Figure 6-23. Signal-to-Noise Ratio vs Input Voltage

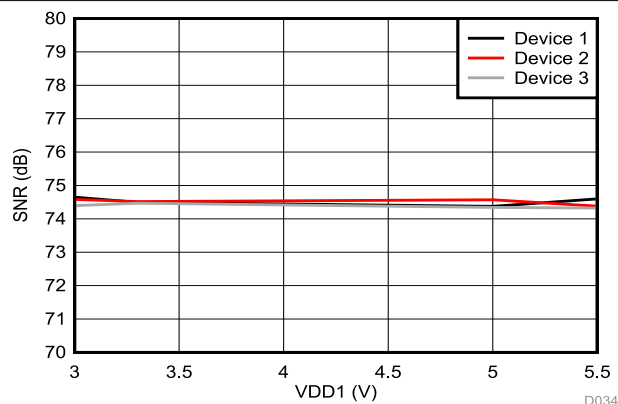


Figure 6-24. Signal-to-Noise Ratio vs High-Side Supply Voltage

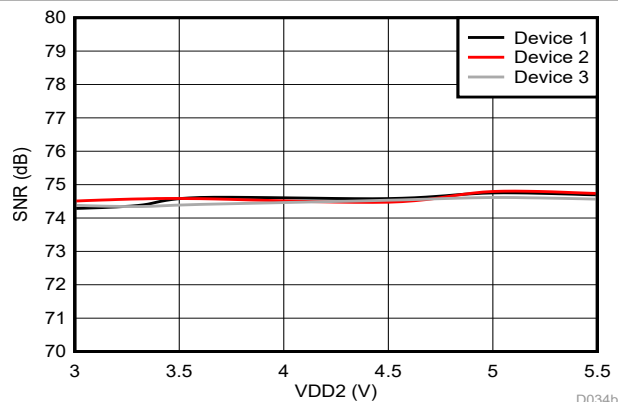


Figure 6-25. Signal-to-Noise Ratio vs Low-Side Supply Voltage

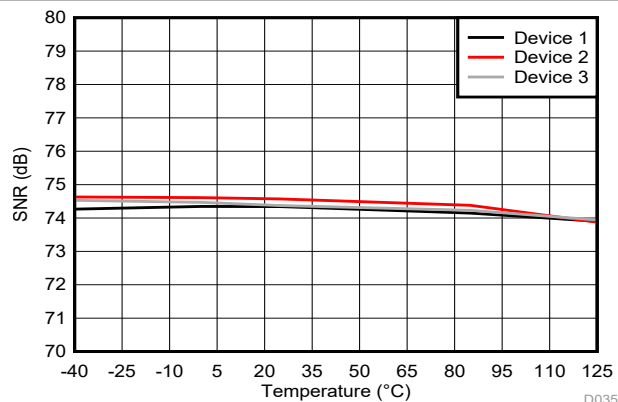


Figure 6-26. Signal-to-Noise Ratio vs Temperature

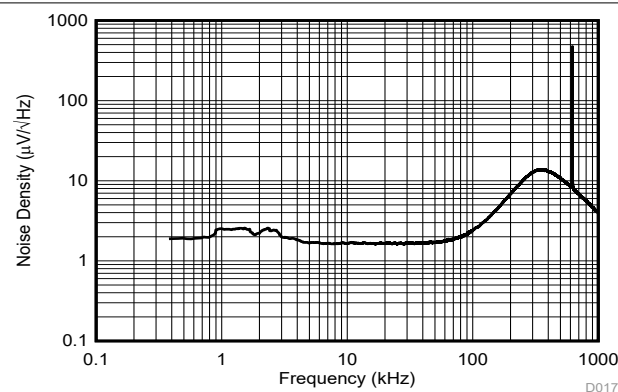


Figure 6-27. Input-Referred Noise Density vs Frequency

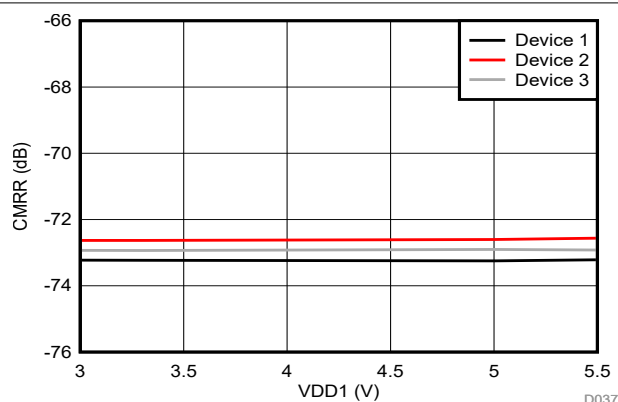
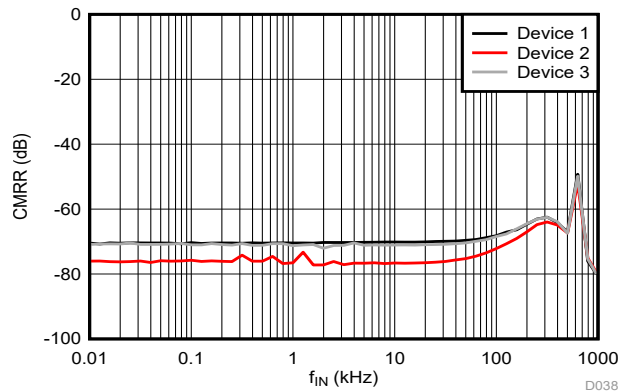


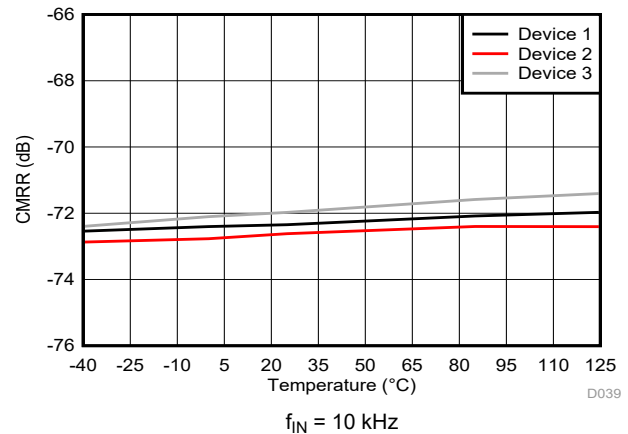
Figure 6-28. Common-Mode Rejection Ratio vs Supply Voltage

6.13 Typical Characteristics (continued)

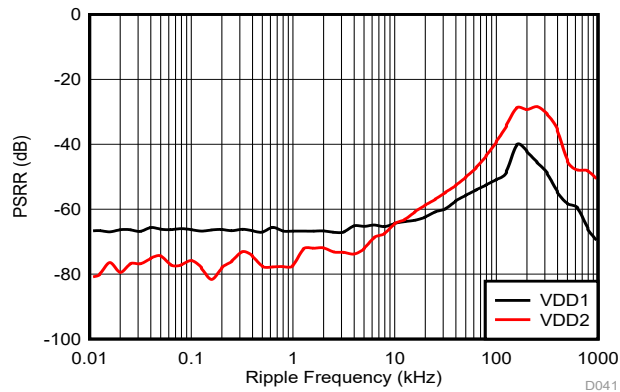
at VDD1 = 5 V, VDD2 = 3.3 V, INN = GND1, INP = -5 V to 5 V, and $f_{IN} = 10$ kHz (unless otherwise noted)



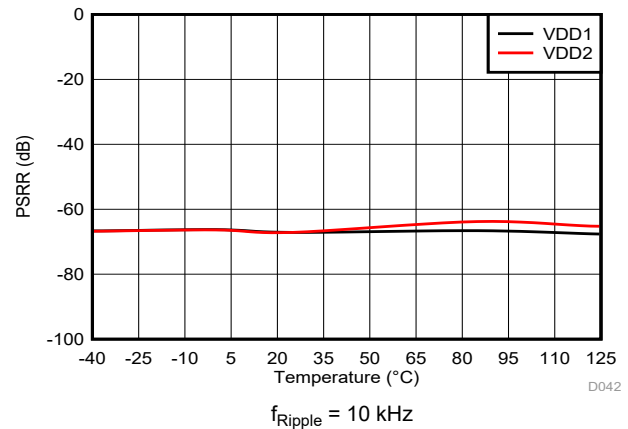
6-29. Common-Mode Rejection Ratio vs Input Frequency



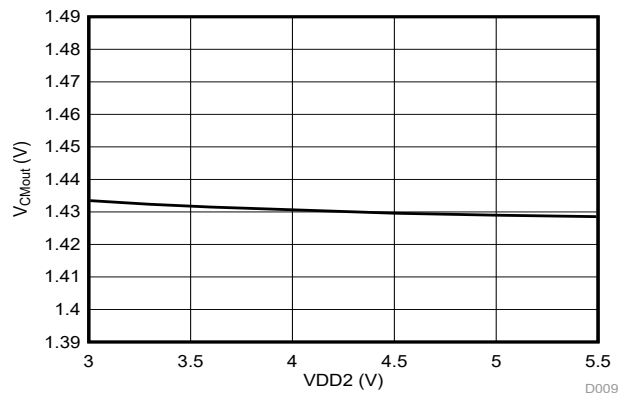
6-30. Common-Mode Rejection Ratio vs Temperature



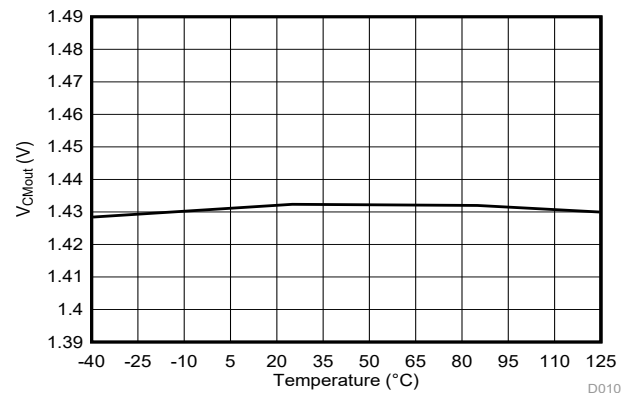
6-31. Power-Supply Rejection Ratio vs Ripple Frequency



6-32. Power-Supply Rejection Ratio vs Temperature



6-33. Common-Mode Output Voltage vs Supply Voltage



6-34. Common-Mode Output Voltage vs Temperature

6.13 Typical Characteristics (continued)

at VDD1 = 5 V, VDD2 = 3.3 V, INN = GND1, INP = -5 V to 5 V, and $f_{IN} = 10$ kHz (unless otherwise noted)

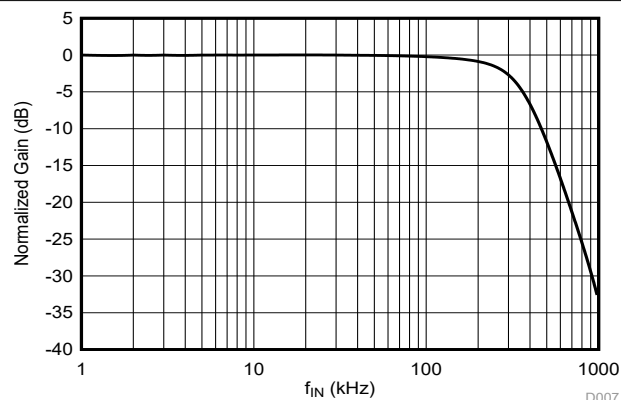


Figure 6-35. Normalized Gain vs Input Frequency

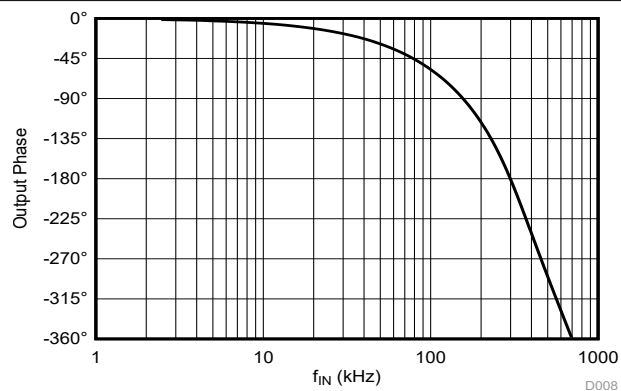


Figure 6-36. Output Phase vs Input Frequency

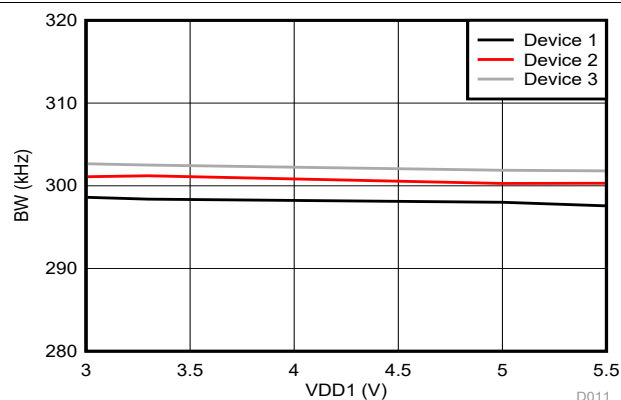


Figure 6-37. Bandwidth vs Supply Voltage

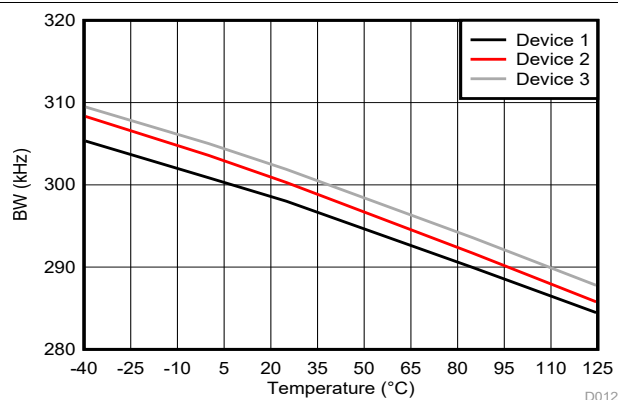


Figure 6-38. Bandwidth vs Temperature

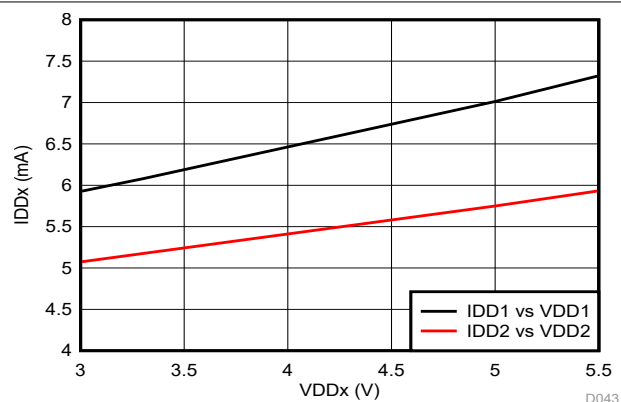


Figure 6-39. Supply Current vs Supply Voltage

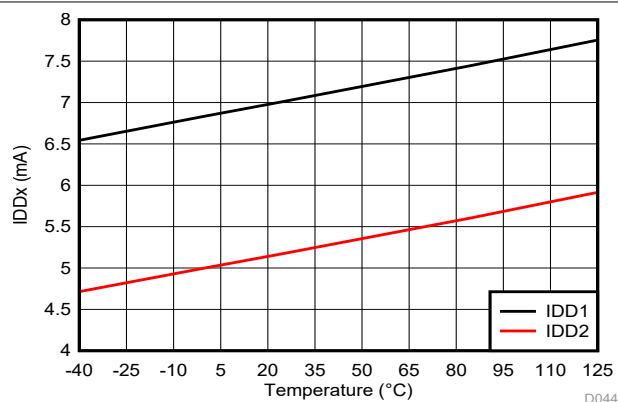
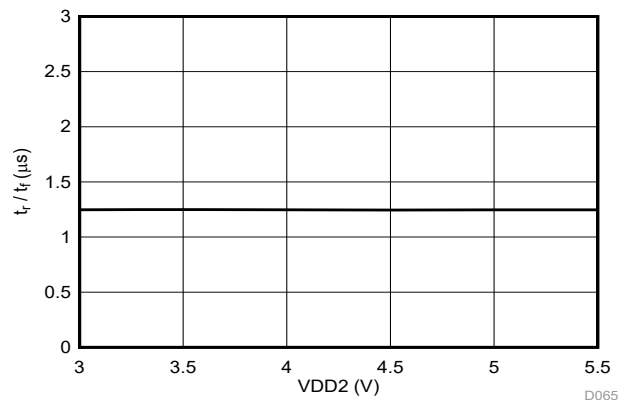


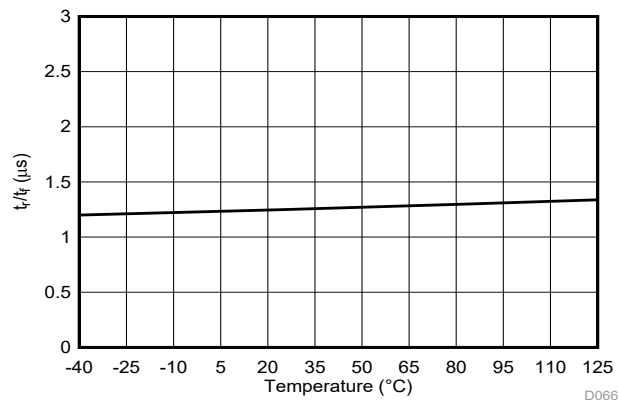
Figure 6-40. Supply Current vs Temperature

6.13 Typical Characteristics (continued)

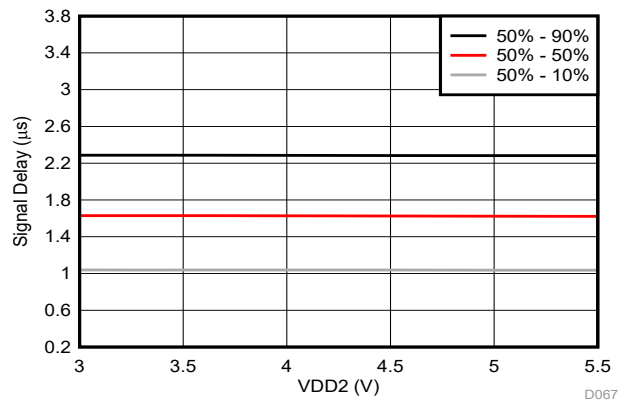
at VDD1 = 5 V, VDD2 = 3.3 V, INN = GND1, INP = -5 V to 5 V, and $f_{IN} = 10$ kHz (unless otherwise noted)



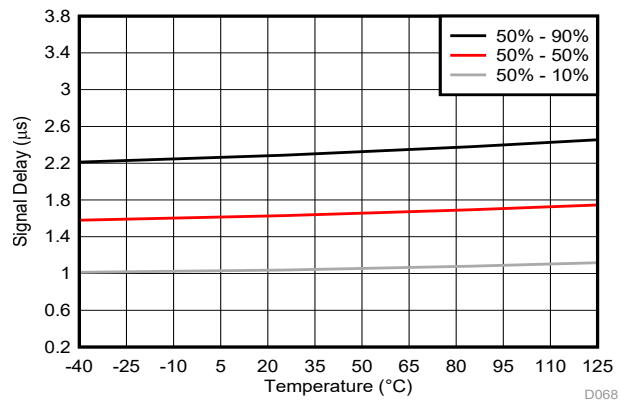
6-41. Output Rise and Fall Time vs Supply Voltage



6-42. Output Rise and Fall Time vs Temperature



6-43. Input to Output Signal Delay vs Supply Voltage



6-44. Input to Output Signal Delay vs Temperature

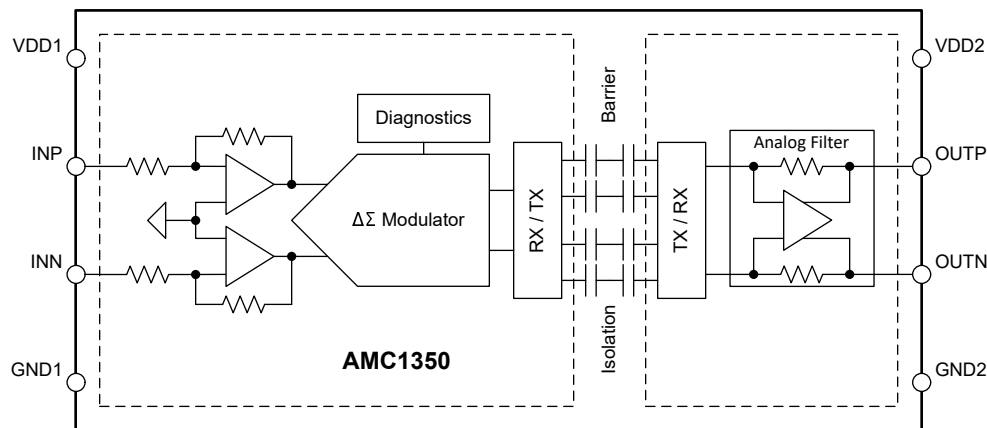
7 Detailed Description

7.1 Overview

The AMC1350 is a fully differential, precision, isolated amplifier with high input impedance. The input stage of the device consists of a fully differential amplifier that drives a second-order, delta-sigma ($\Delta\Sigma$) modulator. The modulator converts the analog input signal into a digital bitstream that is transferred across the isolation barrier that separates the high-side from the low-side. On the low-side, the received bitstream is processed by a fourth-order analog filter that outputs a differential signal at the OUTP and OUTN pins proportional to the input signal.

The SiO₂-based, capacitive isolation barrier supports a high level of magnetic field immunity, as described in the [ISO72x Digital Isolator Magnetic-Field Immunity application report](#). The digital modulation used in the AMC1350 to transmit data across the isolation barrier, and the isolation barrier characteristics itself, result in high reliability and common-mode transient immunity.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Analog Input

The single-ended, high-impedance input stage of the AMC1350 feeds a second-order, switched-capacitor, feed-forward $\Delta\Sigma$ modulator. The modulator converts the analog signal into a bitstream that is transferred across the isolation barrier, as described in the [Isolation Channel Signal Transmission](#) section.

There are two restrictions on the analog input signals INP and INN. First, if the input voltages V_{INP} or V_{INN} exceed the range specified in the [Absolute Maximum Ratings](#) table, the input currents must be limited to the absolute maximum value because the electrostatic discharge (ESD) protection turns on. In addition, the linearity and parametric performance of the device are ensured only when the analog input voltage remains within the linear full-scale range (V_{FSR}) and within the common-mode input voltage range (V_{CM}) as specified in the [Recommended Operating Conditions](#) table.

7.3.2 Isolation Channel Signal Transmission

The AMC1350 uses an on-off keying (OOK) modulation scheme, as shown in [Figure 7-1](#), to transmit the modulator output bitstream across the SiO₂-based isolation barrier. The transmit driver (TX) shown in the [Functional Block Diagram](#) transmits an internally-generated, high-frequency carrier across the isolation barrier to represent a digital *one* and does not send a signal to represent a digital *zero*. The nominal frequency of the carrier used inside the AMC1350 is 480 MHz.

The receiver (RX) on the other side of the isolation barrier recovers and demodulates the signal and provides the input to the fourth-order analog filter. The AMC1350 transmission channel is optimized to achieve the highest level of common-mode transient immunity (CMTI) and lowest level of radiated emissions caused by the high-frequency carrier and RX/TX buffer switching.

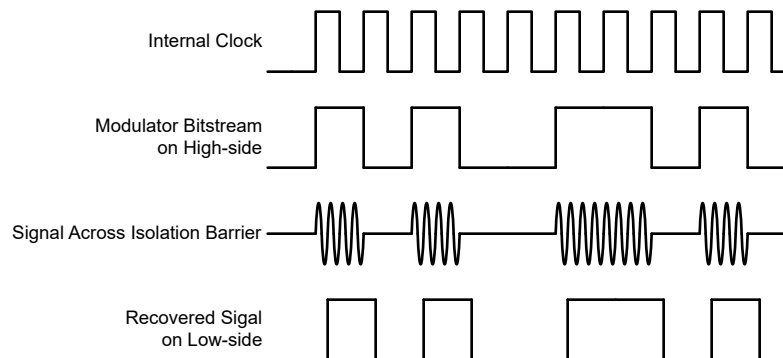


Figure 7-1. OOK-Based Modulation Scheme

7.3.3 Analog Output

The AMC1350 offers a differential analog output on the OUTP and OUTN pins. For differential input voltages ($V_{INP} - V_{INN}$) in the range from -5 V to $+5\text{ V}$, the device provides a linear response with a nominal gain of 0.4 V/V . For example, for a differential input voltage of 5 V , the differential output voltage ($V_{OUTP} - V_{OUTN}$) is 2 V . At zero input (INP shorted to INN), both pins output the same common-mode output voltage V_{CMout} , as specified in the [Electrical Characteristics](#) table. For absolute differential input voltages greater than 5 V but less than 5.75 V , the differential output voltage continues to increase in magnitude but with reduced linearity performance. The outputs saturate at a differential output voltage of $V_{CLIPout}$, as shown in [Figure 7-2](#), if the differential input voltage exceeds the $V_{Clipping}$ value.

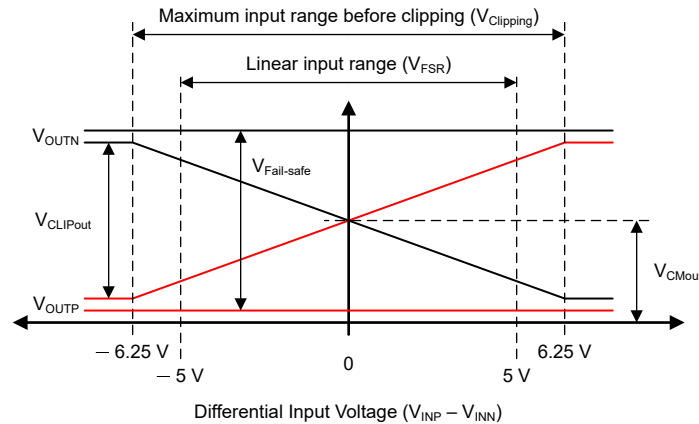


Figure 7-2. Output Behavior of the AMC1350

The AMC1350 output offers a fail-safe feature that simplifies diagnostics on a system level. [Figure 7-2](#) shows the fail-safe condition, in which the AMC1350 outputs a negative differential output voltage that does not occur under normal operating conditions. The fail-safe output is active in two cases:

- When the high-side supply $VDD1$ of the AMC1350 device is missing
- When the high-side supply $VDD1$ falls below the undervoltage threshold $VDD1_{UV}$

Use the maximum $V_{Fail-safe}$ voltage specified in the [Electrical Characteristics](#) table as a reference value for fail-safe detection on a system level.

7.4 Device Functional Modes

The AMC1350 is operational when the power supplies $VDD1$ and $VDD2$ are applied as specified in the [Recommended Operating Conditions](#) table.

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The high input impedance, low input bias current, bipolar input voltage range, excellent accuracy, and low temperature drift make the AMC1350 a high-performance solution for industrial applications where isolated AC or DC voltage sensing is required.

8.2 Typical Application

Isolated amplifiers are widely used for voltage measurements in high-voltage applications that must be isolated from a low-voltage domain. Typical applications are AC line voltage measurements, either line-to-neutral or line-to-line in grid-connected equipment.

✉ **8-1** illustrates a simplified schematic of a solar inverter application that uses three AMC1350 devices to measure the AC line voltage on each phase of a three-phase system. The AC line voltage is divided down to an approximate ± 5 -V level across the bottom resistor (RSNS) of a high-impedance resistive divider that is sensed by the AMC1350. The output of the AMC1350 is a differential analog output voltage proportional to the input voltage but is galvanically isolated from the high-side by a reinforced isolation barrier. A common high-side power supply (VDD1) for all three AMC1350 devices is generated from the low-side supply (VDD2) of the system by an isolated DC/DC converter circuit. A low-cost solution is based on the push-pull driver [SN6501](#) and a transformer that supports the desired isolation voltage ratings.

The high-impedance input, high input voltage range, and the high common-mode transient immunity (CMTI) of the AMC1350 ensure reliable and accurate operation even in high-noise environments.



8.2.1 Design Requirements

表 8-1 lists the parameters for this typical application.

表 8-1. Design Requirements

PARAMETER	120-V _{RMS} LINE VOLTAGE	230-V _{RMS} LINE VOLTAGE
System input voltage	120 V ±10%, 60 Hz	230 V ±10%, 50 Hz
High-side supply voltage	3.3 V or 5 V	3.3 V or 5 V
Low-side supply voltage	3.3 V or 5 V	3.3 V or 5 V
Maximum resistor operating voltage	75 V	75 V
Voltage drop across the sense resistor (RSNS) for a linear response	±5 V (maximum)	±5 V (maximum)
Current through the resistive divider, I _{CROSS}	100 µA	100 µA

8.2.2 Detailed Design Procedure

This discussion covers the 230-V_{RMS} example. The procedure for calculating the resistive divider for the 120-V_{RMS} use case is identical.

The 100-µA, cross-current requirement at peak input voltage (360 V) determines that the total impedance of the resistive divider is 3.6 MΩ. The impedance of the resistive divider is dominated by the top resistors (shown exemplary as R1 and R2 in 图 8-1) and the voltage drop across RSNS can be neglected for a short time. The maximum allowed voltage drop per unit resistor is specified as 75 V; therefore, the total minimum number of unit resistors in the top portion of the resistive divider is 360 V / 75 V = 5. The calculated unit value is 3.6 MΩ / 5 = 720 kΩ and the next closest value from the E96 series is 715 kΩ.

The *effective* sense resistor value RSNS_{EFF} is the parallel combination of the external resistor RSNS and the input impedance of the AMC1350, R_{IN}. RSNS_{EFF} is sized such that the voltage drop across the impedance at maximum input voltage (360 V) equals the linear full-scale input voltage (V_{FSR}) of the AMC1350 (that is, +5 V). RSNS_{EFF} is calculated as $RSNS_{EFF} = V_{FSR} / (V_{Peak} - V_{FSR}) \times R_{TOP}$ where R_{TOP} is the total value of the top resistor string (5 × 715 kΩ = 3575 kΩ). The resulting value for RSNS_{EFF} is 9.96 kΩ. In a final step, RSNS is calculated as $RSNS = R_{IN} \times RSNS_{EFF} / (R_{IN} - RSNS_{EFF})$. With R_{IN} = 1.25 MΩ (typical), RSNS equals 52.47 kΩ and the next closest value from the E96 series is 52.3 kΩ.

表 8-2 summarizes the design of the resistive divider.

表 8-2. Resistor Value Examples

PARAMETER	120-V _{RMS} LINE VOLTAGE	230-V _{RMS} LINE VOLTAGE
Peak voltage	190 V	360 V
Unit resistor value, R _{TOP}	634 kΩ	715 kΩ
Number of unit resistors in R _{TOP}	3	5
Sense resistor value, RSNS	53.6 kΩ	52.3 kΩ
Total resistance value (R _{TOP} + RSNS)	1953.4 kΩ	3625.2 kΩ
Resulting current through resistive divider, I _{CROSS}	97.3 µA	99.3 µA
Resulting full-scale voltage drop across sense resistor RSNS	4.993 V	4.982 V
Peak power dissipated in R _{TOP} unit resistor	6 mW	7.1 mW
Total peak power dissipated in resistive divider	18.5 mW	35.7 mW

8.2.2.1 Input Filter Design

Placing an RC filter in front of the isolated amplifier improves signal-to-noise performance of the signal path. In practice, however, the impedance of the resistor divider is so high that adding a filter capacitor on the INN or INP pin limits the signal bandwidth to an unacceptable low limit, such that the filter capacitor is omitted. When used, design the input filter such that:

- The cutoff frequency of the filter is at least one order of magnitude lower than the sampling frequency (20 MHz) of the internal $\Delta\Sigma$ modulator
- The input bias current does not generate significant voltage drop across the DC impedance of the input filter

Most voltage-sensing applications use high-impedance resistor dividers in front of the isolated amplifier to scale down the input voltage. In that case, no additional resistor is needed and a single capacitor (as shown in [Figure 8-2](#)) is sufficient to filter the input signal.

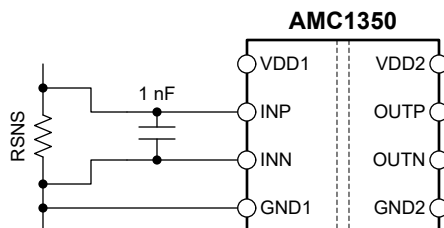


Figure 8-2. Input Filter

8.2.2.2 Differential to Single-Ended Output Conversion

[Figure 8-3](#) shows an example of a TLV6001-based signal conversion and filter circuit for systems using single-ended input ADCs to convert the analog output voltage into digital. With $R1 = R2 = R3 = R4$, the output voltage equals $(V_{OUTP} - V_{OUTN}) + V_{REF}$. Tailor the bandwidth of this filter stage to the bandwidth requirement of the system and use NP0-type capacitors for best performance. For most applications, $R1 = R2 = R3 = R4 = 3.3 \text{ k}\Omega$ and $C1 = C2 = 330 \text{ pF}$ yields good performance.

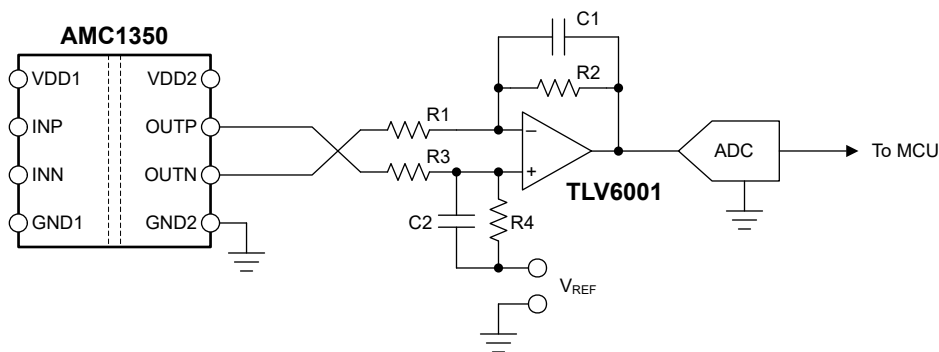


Figure 8-3. Connecting the AMC1350 Output to a Single-Ended Input ADC

For more information on the general procedure to design the filtering and driving stages of SAR ADCs, see the [18-Bit, 1MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Distortion and Noise](#) and [18-Bit Data Acquisition Block \(DAQ\) Optimized for Lowest Power reference guides](#), available for download at www.ti.com.

8.2.3 Application Curve

One important aspect of system design is the effective detection of an overvoltage condition to protect switching devices and passive components from damage. To power off the system quickly in the event of an overvoltage condition, a low delay caused by the isolated amplifier is required. [Figure 8-4](#) shows the typical full-scale step response of the AMC1350.

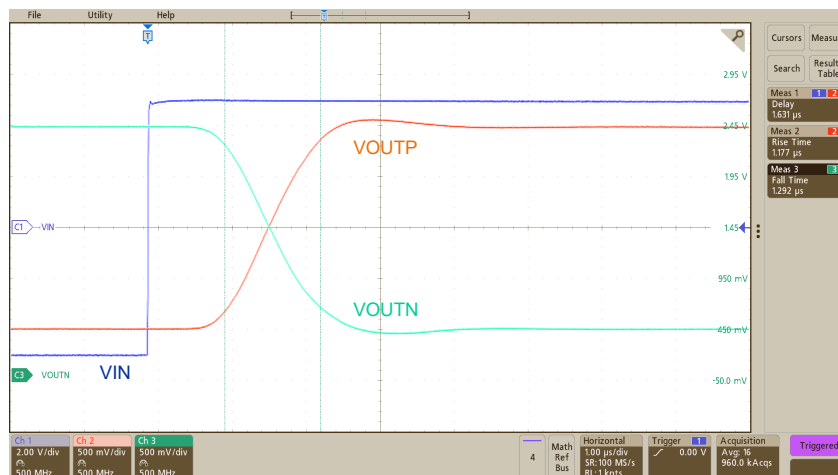


Figure 8-4. Step Response of the AMC1350

8.3 What To Do and What Not To Do

Do not leave the inputs of the AMC1350 unconnected (floating) when the device is powered up. If the device inputs are left floating, the input bias current may drive the inputs to a positive or negative value that exceeds the operating common-mode input voltage and the device output is undetermined.

Connect the high-side ground (GND1) to INN, either by a hard short or through a resistive path. A DC current path between INN and GND1 is required to define the input common-mode voltage. Take care not to exceed the input common-mode range as specified in the [Recommended Operating Conditions](#) table. For best accuracy, route the ground connection as a separate trace that connects directly to the sense resistor rather than shorting GND1 to INN directly at the input to the device. See the [Layout](#) section for more details.

Do not connect protection diodes to the inputs (INP or INN) of the AMC1350. Diode leakage current can introduce significant measurement error especially at high temperatures. The input pin is protected against high voltages by its ESD protection circuit and the high impedance of the external resistive divider.

9 Power Supply Recommendations

In a typical application, the high-side power supply (VDD1) for the AMC1350 is generated from the low-side supply (VDD2) by an isolated DC/DC converter. A low-cost solution is based on the push-pull driver [SN6501](#) and a transformer that supports the desired isolation voltage ratings.

The AMC1350 does not require any specific power-up sequencing. The high-side power supply (VDD1) is decoupled with a low-ESR, 100-nF capacitor (C1) parallel to a low-ESR, 1-μF capacitor (C2). The low-side power supply (VDD2) is equally decoupled with a low-ESR, 100-nF capacitor (C3) parallel to a low-ESR, 1-μF capacitor (C4). Place all four capacitors (C1, C2, C3, and C4) as close to the device as possible. [Figure 9-1](#) shows a decoupling diagram for the AMC1350.

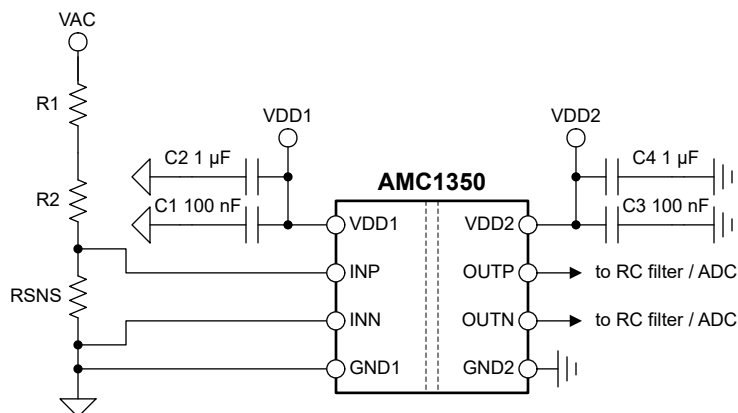


Figure 9-1. Decoupling of the AMC1350

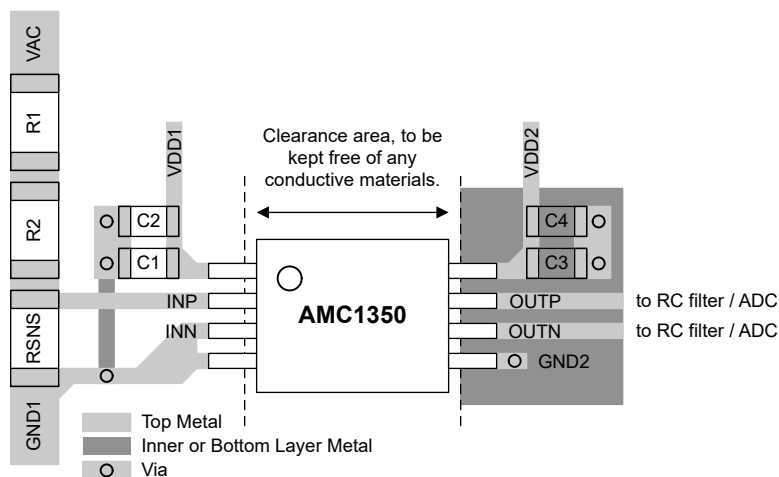
Capacitors must provide adequate effective capacitance under the applicable DC bias conditions they experience in the application. Multilayer ceramic capacitors (MLCC) typically exhibit only a fraction of their nominal capacitance under real-world conditions and this factor must be taken into consideration when selecting these capacitors. This problem is especially acute in low-profile capacitors, in which the dielectric field strength is higher than in taller components. Reputable capacitor manufacturers provide capacitance versus DC bias curves that greatly simplify component selection.

10 Layout

10.1 Layout Guidelines

☒ 10-1 shows a layout recommendation with the critical placement of the decoupling capacitors (as close as possible to the AMC1350 supply pins) and placement of the other components required by the device. For best performance, place the sense resistor close to the device input pin (IN).

10.2 Layout Example



☒ 10-1. Recommended Layout of the AMC1350

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [Isolation Glossary application report](#)
- Texas Instruments, [Semiconductor and IC Package Thermal Metrics application report](#)
- Texas Instruments, [ISO72x Digital Isolator Magnetic-Field Immunity application report](#)
- Texas Instruments, [TLV600x Low-Power, Rail-to-Rail In/Out, 1-MHz Operational Amplifier for Cost-Sensitive Systems data sheet](#)
- Texas Instruments, [TPS763 Low-Power, 150-mA, Low-Dropout Linear Regulator data sheet](#)
- Texas Instrument, [SN6501 Transformer Driver for Isolated Power Supplies data sheet](#)
- Texas Instruments, [18-Bit, 1-MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Distortion and Noise reference guide](#)
- Texas Instruments, [18-Bit, 1-MSPS Data Acquisition Block \(DAQ\) Optimized for Lowest Power reference guide](#)
- Texas Instruments, [Isolated Amplifier Voltage Sensing Excel Calculator design tool](#)
- Texas Instruments, [Best in Class Radiated Emissions EMI Performance with the AMC1300B-Q1 Isolated Amplifier technical white paper](#)

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 サポート・リソース

TI E2E™ サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するものではなく、必ずしも TI の見解を反映したものではありません。TI の[使用条件](#)を参照してください。

11.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
AMC1350DWV	Active	Production	SOIC (DWV) 8	64 TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC1350
AMC1350DWV.A	Active	Production	SOIC (DWV) 8	64 TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC1350
AMC1350DWV.B	Active	Production	SOIC (DWV) 8	64 TUBE	-	Call TI	Call TI	-40 to 125	
AMC1350DWVR	Active	Production	SOIC (DWV) 8	1000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC1350
AMC1350DWVR.A	Active	Production	SOIC (DWV) 8	1000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC1350
AMC1350DWVR.B	Active	Production	SOIC (DWV) 8	1000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
AMC1350DWVRG4	Active	Production	SOIC (DWV) 8	1000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC1350
AMC1350DWVRG4.A	Active	Production	SOIC (DWV) 8	1000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	AMC1350
AMC1350DWVRG4.B	Active	Production	SOIC (DWV) 8	1000 LARGE T&R	-	Call TI	Call TI	-40 to 125	

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative

and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

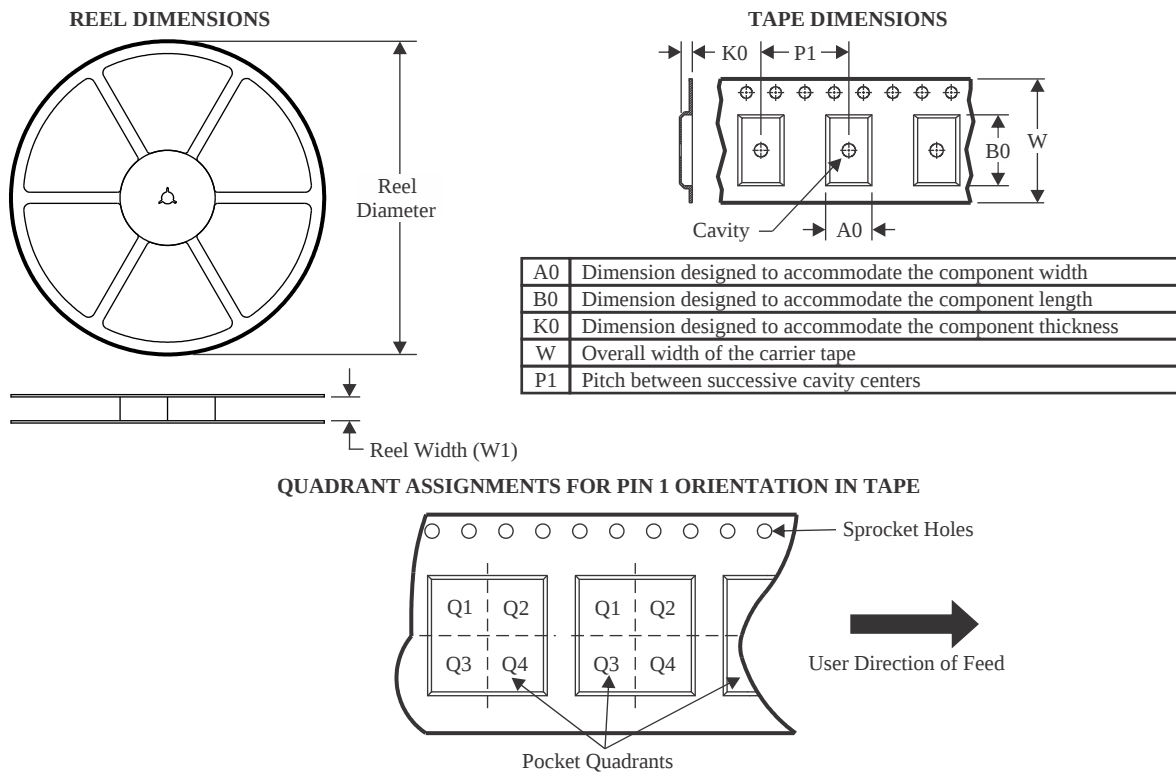
OTHER QUALIFIED VERSIONS OF AMC1350 :

- Automotive : [AMC1350-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

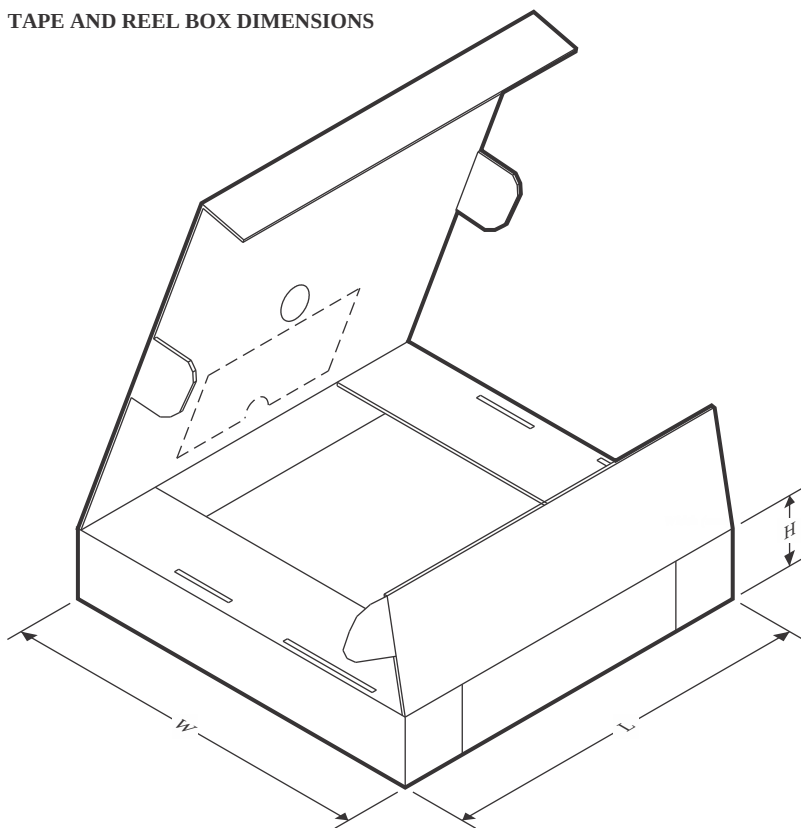
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
AMC1350DWVR	SOIC	DWV	8	1000	330.0	16.4	12.15	6.2	3.05	16.0	16.0	Q1
AMC1350DWVRG4	SOIC	DWV	8	1000	330.0	16.4	12.05	6.15	3.3	16.0	16.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
AMC1350DWVR	SOIC	DWV	8	1000	353.0	353.0	32.0
AMC1350DWVRG4	SOIC	DWV	8	1000	350.0	350.0	43.0

TUBE

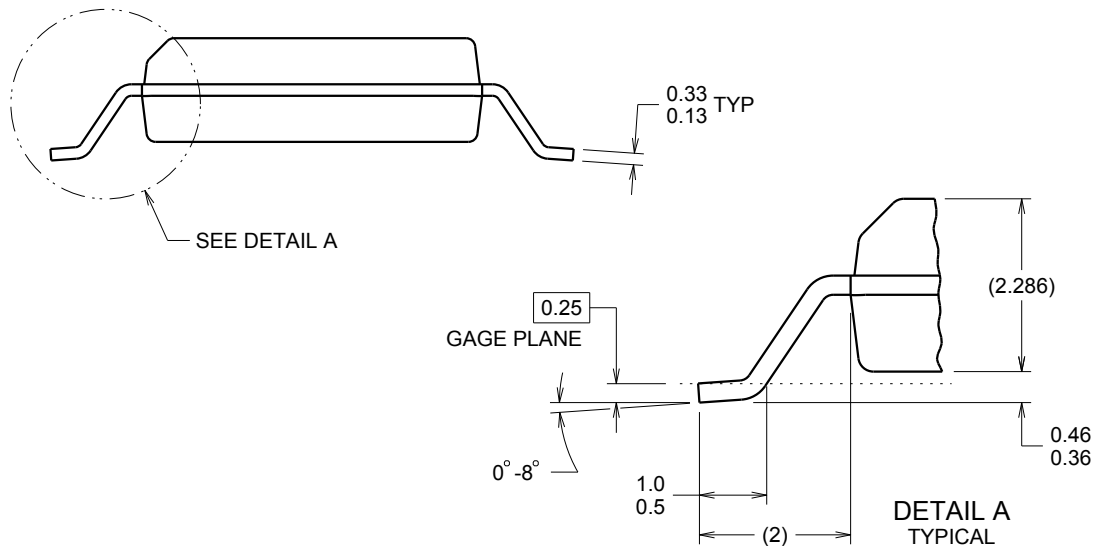


*All dimensions are nominal

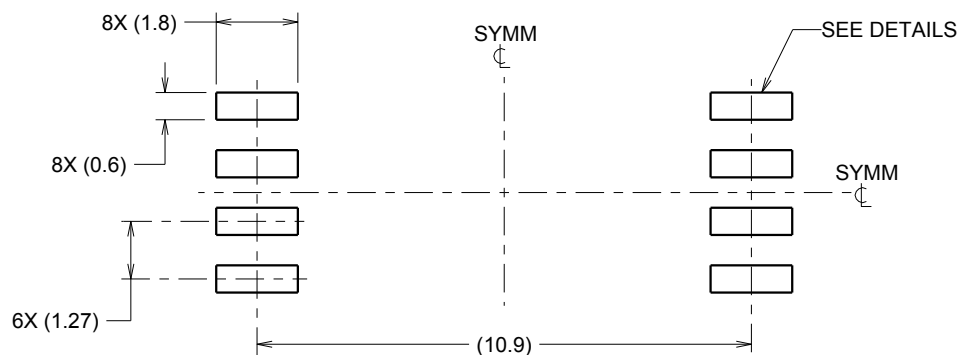
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
AMC1350DWV	DWV	SOIC	8	64	505.46	13.94	4826	6.6
AMC1350DWV.A	DWV	SOIC	8	64	505.46	13.94	4826	6.6

SOIC - 2.8 mm max height

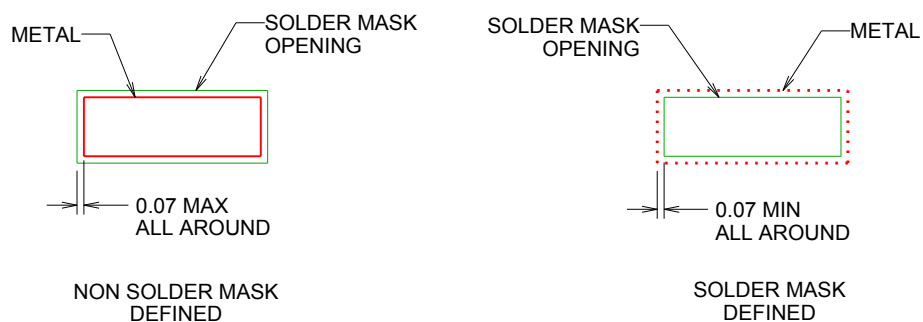
PIN 1 ID AREA
 11.5 ± 0.25 TYP
 5.95
 5.75
 NOTE 3
 1
 4
 8
 5
 6X 1.27
 2X 3.81
 8X 0.51
 0.31
 7.6
 7.4
 NOTE 4
 A
 B
 SEATING PLANE
 0.1 C
 2.8 MAX
 C
 A
 B



1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



LAND PATTERN EXAMPLE
9.1 mm NOMINAL CLEARANCE/CREEPAGE
SCALE:6X

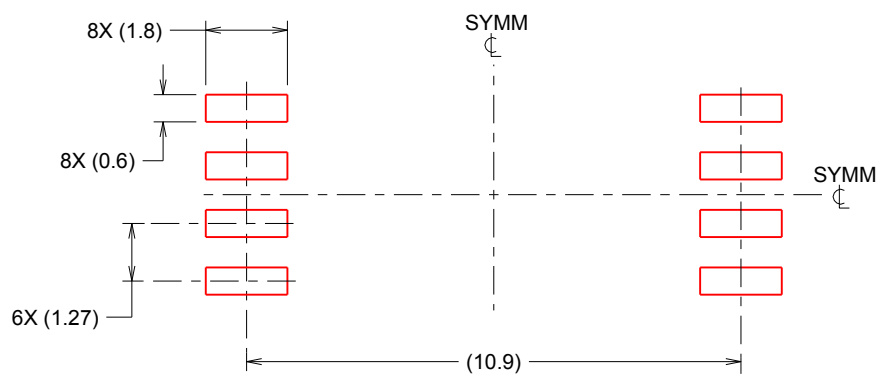


SOLDER MASK DETAILS

4218796/A 09/2013

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL
 SCALE:6X

4218796/A 09/2013

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

重要なお知らせと免責事項

テキサス・インスツルメンツは、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、テキサス・インスツルメンツ製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した テキサス・インスツルメンツ製品の選定、(2) お客様のアプリケーションの設計、検証、試験、(3) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとします。

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている テキサス・インスツルメンツ製品を使用するアプリケーションの開発の目的でのみ、テキサス・インスツルメンツはその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。テキサス・インスツルメンツや第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、テキサス・インスツルメンツおよびその代理人を完全に補償するものとし、テキサス・インスツルメンツは一切の責任を拒否します。

テキサス・インスツルメンツの製品は、[テキサス・インスツルメンツの販売条件](#)、または [ti.com](https://www.ti.com) やかかる テキサス・インスツルメンツ製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。テキサス・インスツルメンツがこれらのリソースを提供することは、適用される テキサス・インスツルメンツの保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、テキサス・インスツルメンツはそれらに異議を唱え、拒否します。

郵送先住所：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
Copyright © 2025, Texas Instruments Incorporated